Artificial Structures Through Layer-by-Layer Growth

Brent Melot Materials 286G Ram Seshadri Fall 2005

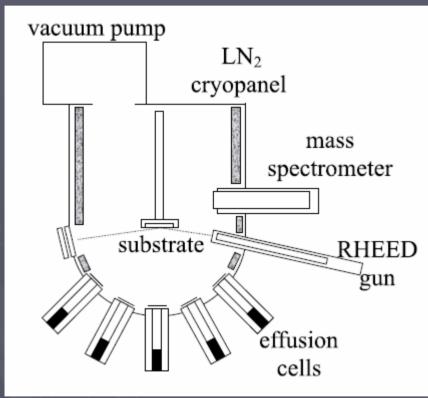
Overview

- ▶ Motivation
- ► Tools for Growth
- ► Factors Influencing Stabilization
- Representative Structures
- Surface Engineering

Motivation

- Structural Control
 - New and Metastable Phases
 - Surface Properties
- Magnetic Tunneling Junctions
- Wear and Oxidation Resistance
- ► Thin Film Transistors
- ► Improved Solar Cells

Molecular Beam Epitaxy

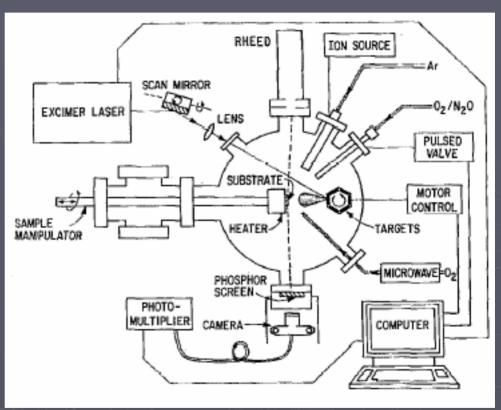


F. Rinaldi. Annual Report 2002, Optoelectronics Department, University of Ulm

- Growth occurs through slow evaporation of components
- Composition controlled through opening and closing of mechanical shutters
 - Allows control to the monolayer level

Pulsed Laser Deposition

- Target consists of stoichiometric pellets of starting materials
- Laser superheats target resulting in a plasma plume that coats the substrate
- Plume has same stoichiometry as pellet



M. Y. Chern, A. Gupta and B. W. Hussey, Appl. Phys. Lett. 60, 3045 (1992)

Thermodynamic Stabilization

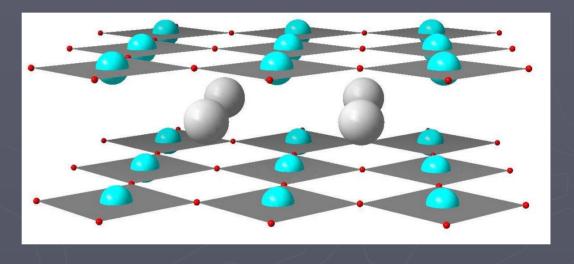
- Stabilization Increases with
 - Decrease of film thickness
 - Increasing coherency between substrate and growing crystal
 - Decrease of shear and elastic moduli of growing crystal
 - Ability to form periodic multiple-domain structures

Kinetic Stabilization

- Determined by growth conditions
 - Substrate temperature, annealing etc
 - ▶ Pt will only wet SrTiO₃ surfaces at low temperatures
- High surface diffusion
 - Enables growth of oriented crystal phases
- Low bulk diffusion
 - Prevents phase transformations

(Ca,Sr)CuO₂

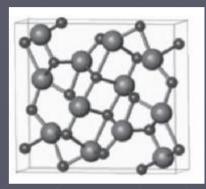
CaCuO₂ is highly metastable and difficult to grow except in layer-by-layer deposition



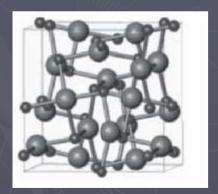
- ► Terminating CuO₂ from SrCuO₂ layer acts as a template that stabilizes and promotes nucleating of CaCuO₂ layers
- ► Creation of (Ca,Sr)CuO₂ layers is fundamental in the creation of superconducting thin films

Cubic-Zr₃N₄

- Grown with a modified filtered cathodic arc (FCA)
 - Metal vapour generated by an arc discharge on pure zirconium cathode reacted with fully ionized atomic nitrogen



orthorombic-Zr₃N₄

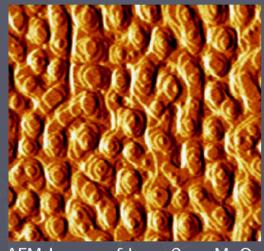


cubic-Zr₃N₄

- ► Bulk growth requires pressures up to 18 GPa and temperatures on the order of 2500-3000K
- Cubic form is significantly harder (~36 GPa) than orthorhombic (~27 GPa)

Surface Properties

Surfaces are not typically smooth

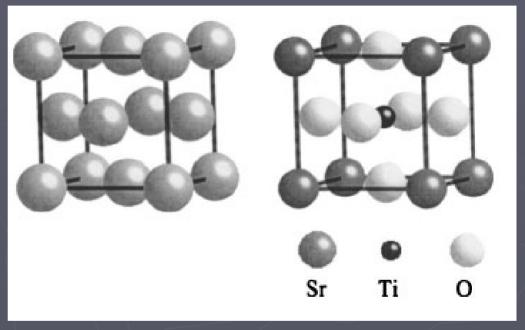


AFM Image of $La_{0.67}Ca_{0.33}MnO_3$ grown on $SrTiO_3$ (001)

- Formation of island structures is common during epitaxial growth
 - Form with increasing film thickness
- Smooth surfaces are desirable for most applications

Surface Properties

▶ Platinum crystallizes in an FCC structure with a very similar shape to that of the perovskite



Unit cell representations of (a) Pt and (b) SrTiO3. Atoms for (b) are indicated.

Surface Properties

- Pt deposited on SrTiO₃
 (6 2 1) exhibits chiral centers at kink points
- Shows great potential for application in catalysis and enantiomeric selection

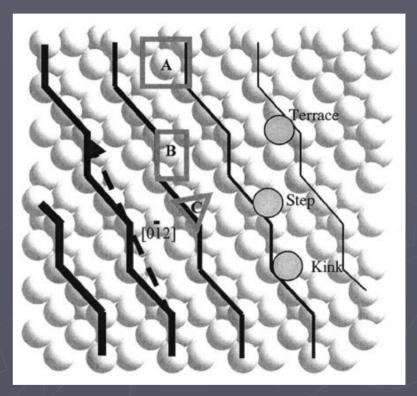


Illustration of surface structure of Pt grown on (6 2 1) SrTiO₃ Bolder lines indicate planes coming out of the board at the viewer

Conclusions

- ► Thin film growth present the opportunity to stabilize phases normally not stable in the bulk
- PLD and MBE allow for robust growth techniques
- Surface structures can be tailored by manipulating the crystallographic angles of the substrate.